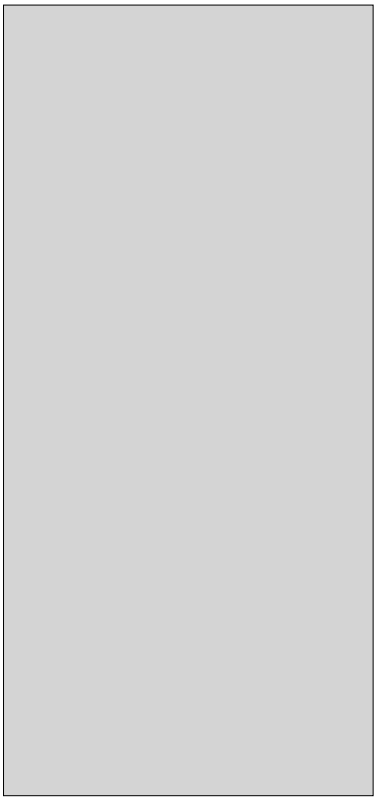
JCT810F 10A SCR

Rev.A.1.1

With high ability to withstand the shock loading of large current, JCT810F of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especiallyrecommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT810F provides a rated insulation voltage of 2000 $V_{RMS,}$ complying with UL standards (File ref: E252906).Package TO-220F is RoHS compliant.



Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	800	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	800	V
Average on-state current ($T_C \leq$ 85)	$I_{T(AV)}$	6.5	A
RMS on-state current ($T_C \leq$ 85)	$I_{T(RMS)}$	10	A
Non repetitive surge peak on-state current (t_p=10ms, T_j=25)	I_{TSM}	110	A

TO-220F(Ins)

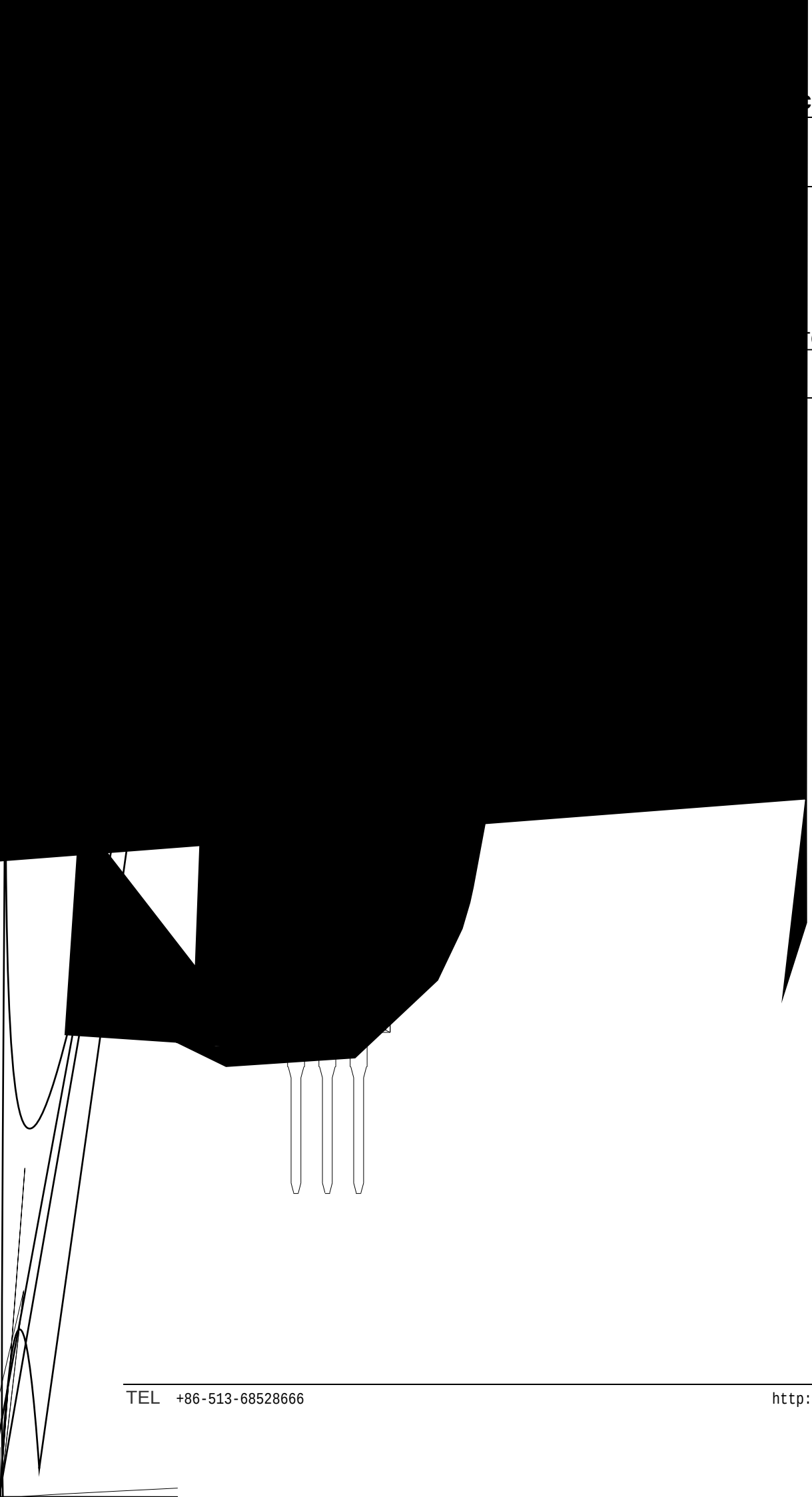


FIG.1: Maximum power dissipation versus RMS on-state current

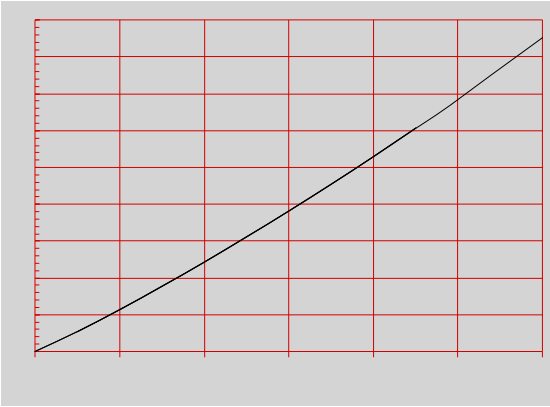


FIG.2: RMS on-state current versus case temperature

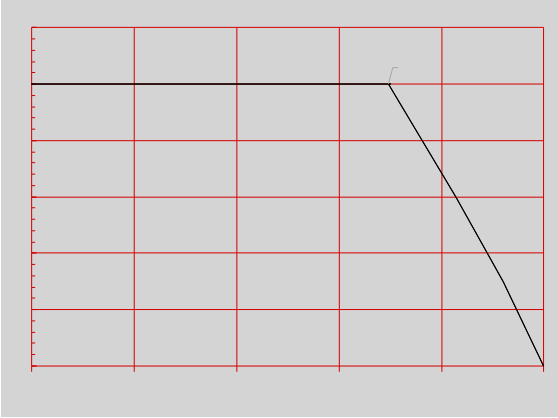
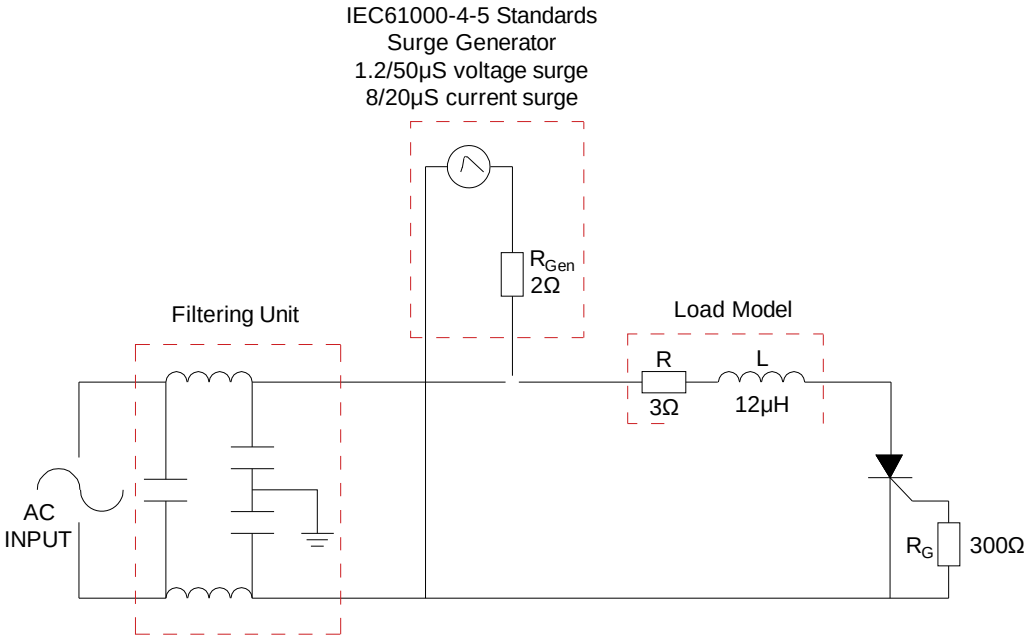
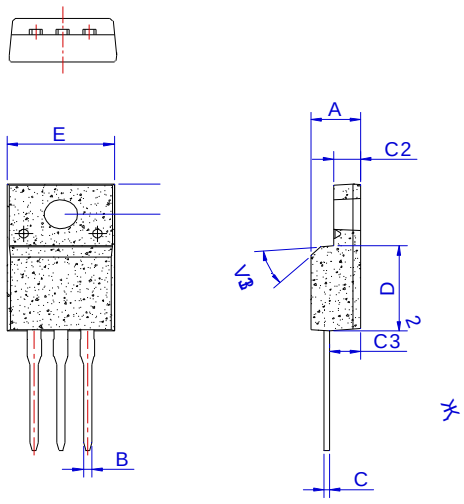


FIG.3: Surge peak on-state current versus number of cycles

FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.




E
A
C2
V3
D
2
C3
B
C